

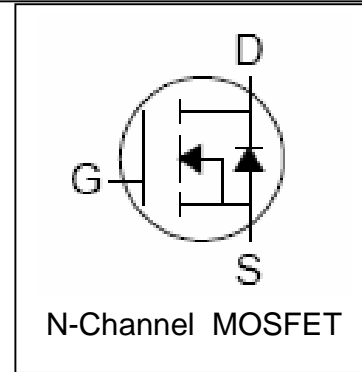
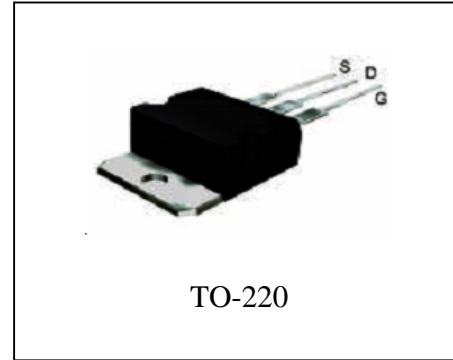
Features

- 65V/80A,
 $R_{DS(ON)} = 8m$ (tpy.) @ $V_{GS} = 10V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- 100% avalanche tested
- Lead Free and Green Devices Available
 (RoHS Compliant)

Applications

- Switching Application Systems
- Inverter Systems

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	65	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ C$ 80 ^①	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C = 25^\circ C$ 320 ^②	A
I_D	Continuous Drain Current	$T_C = 25^\circ C$ 80 ^①	A
		$T_C = 100^\circ C$ 59	
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$ 115	W
		$T_C = 100^\circ C$ 58	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.3	$^\circ C/W$
Drain-Source Avalanche Ratings			
E_{AS} ^③	Avalanche Energy, Single Pulsed	296	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU6588R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	65			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=65V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1	μA
					10	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=40A$		8	9	m Ω
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=40A, V_{GS}=0V$		0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=40A, di_{SD}/dt=100A/\mu s$		31		ns
Q_{rr}	Reverse Recovery Charge			39		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.3		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		2830		pF
C_{oss}	Output Capacitance			320		
C_{riss}	Reverse Transfer Capacitance			195		
$t_{d(ON)}$	Turn-on Delay Time			27		
t_r	Turn-on Rise Time	$V_{DD}=30V, R_L=0.8\Omega,$ $I_{DS}=40A, V_{GEN}=10V,$ $R_G=4.7\Omega$		32		
$t_{d(OFF)}$	Turn-off Delay Time			92		
t_f	Turn-off Fall Time			68		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=52V, V_{GS}=10V,$ $I_{DS}=40A$		60	78	nC
Q_{gs}	Gate-Source Charge			16		
Q_{gd}	Gate-Drain Charge			21		

Notes: ① Calculated continuous current based on maximum allowable junction temperature. Limited by bonding wire.

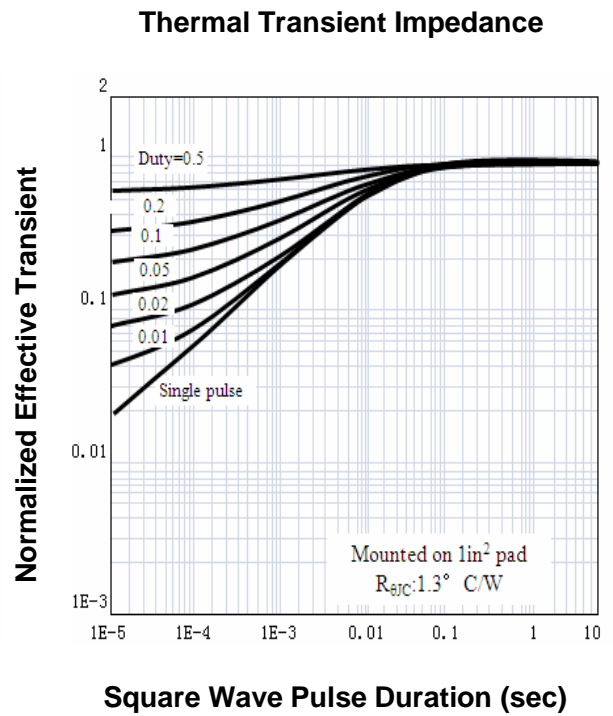
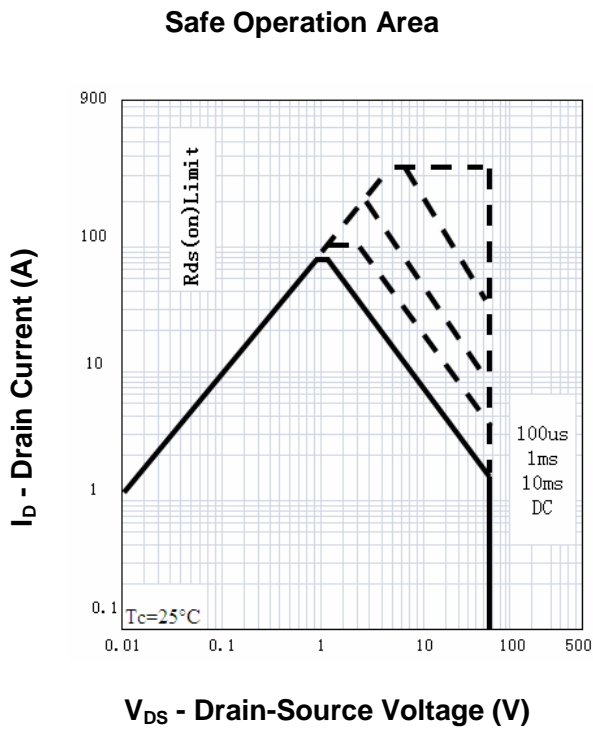
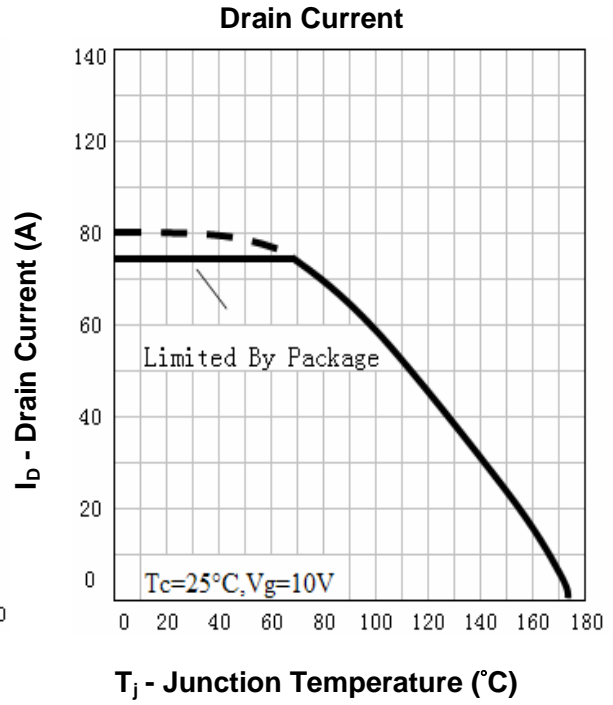
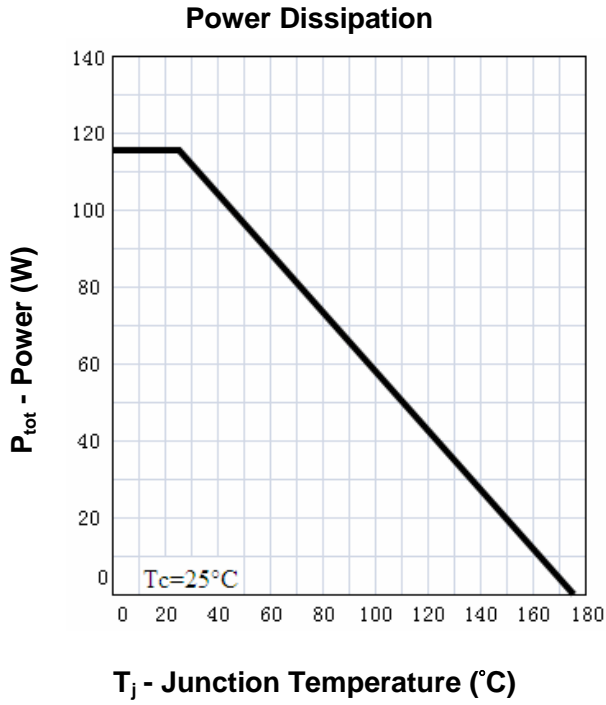
② Pulse width limited by safe operating area.

③ Limited by $T_{Jmax}, I_{AS}=28A, V_{DD}=48V, R_G=50\Omega$, Starting $T_J=25^\circ\text{C}$.

④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

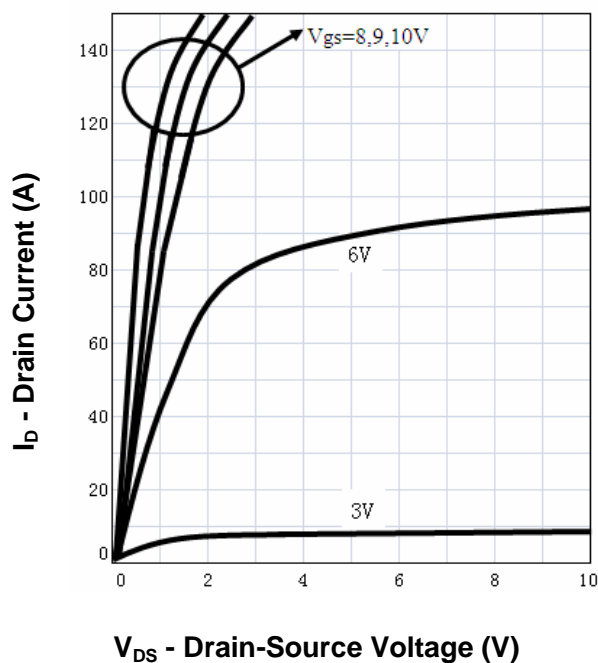
⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

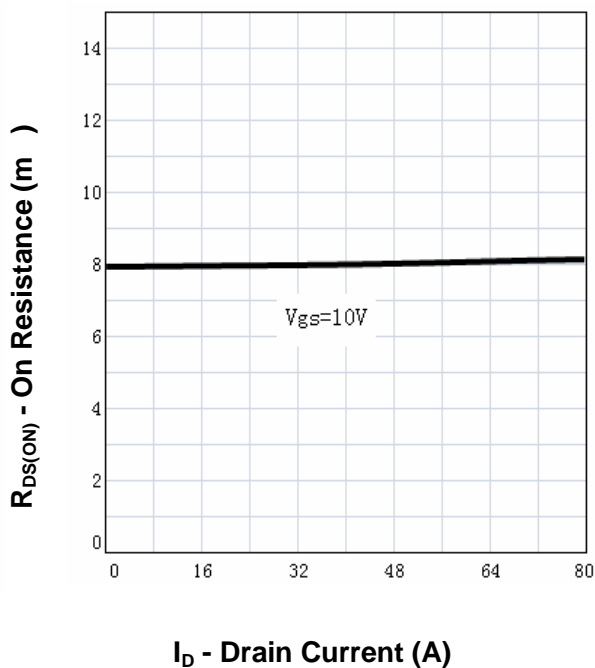


Typical Characteristics

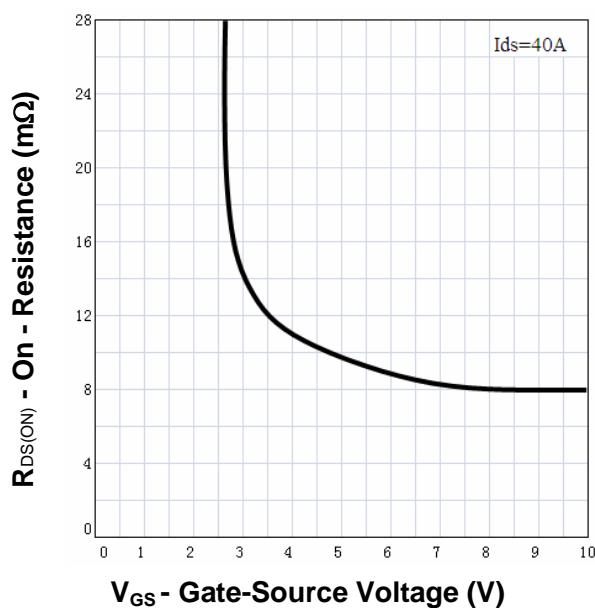
Output Characteristics



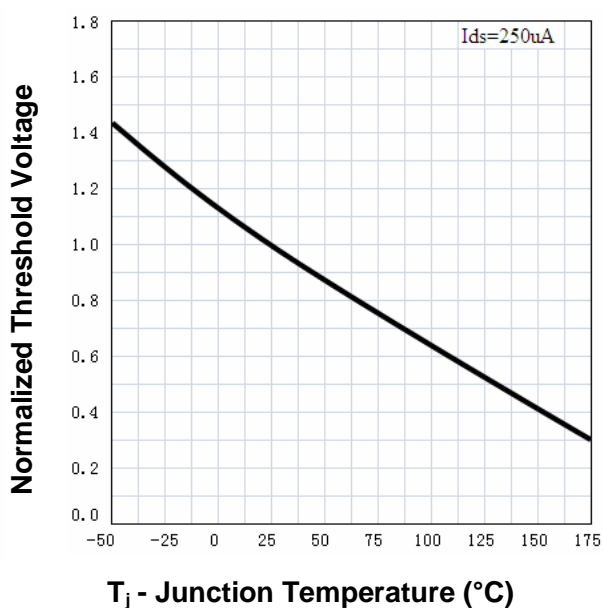
Drain-Source On Resistance



Drain-Source On Resistance

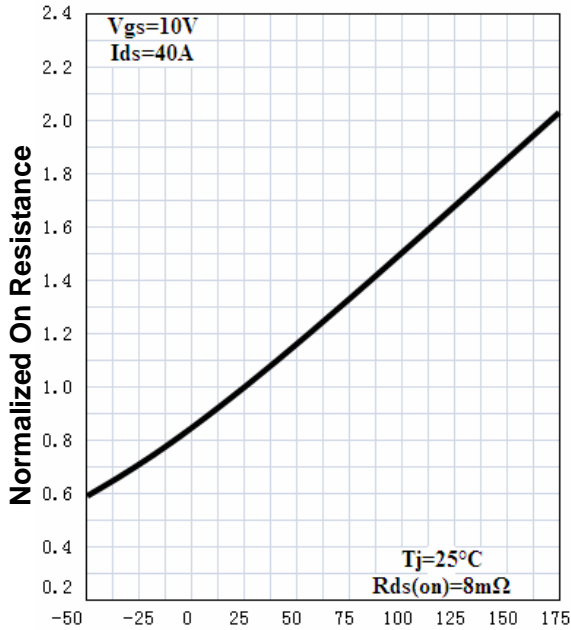


Gate Threshold Voltage



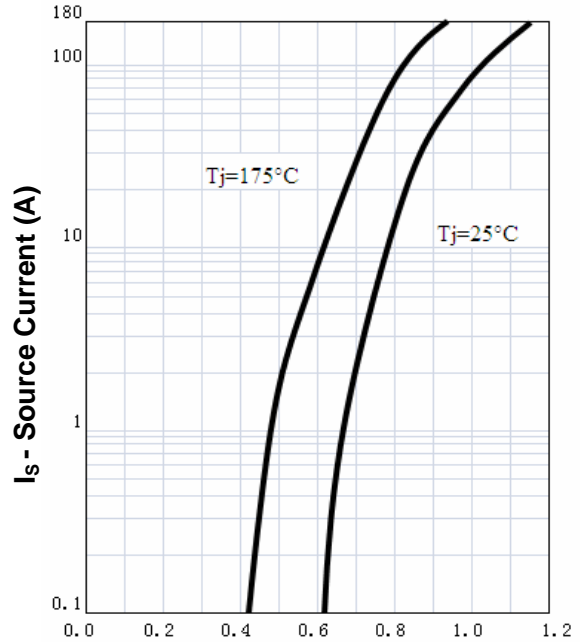
Typical Characteristics

Drain-Source On Resistance



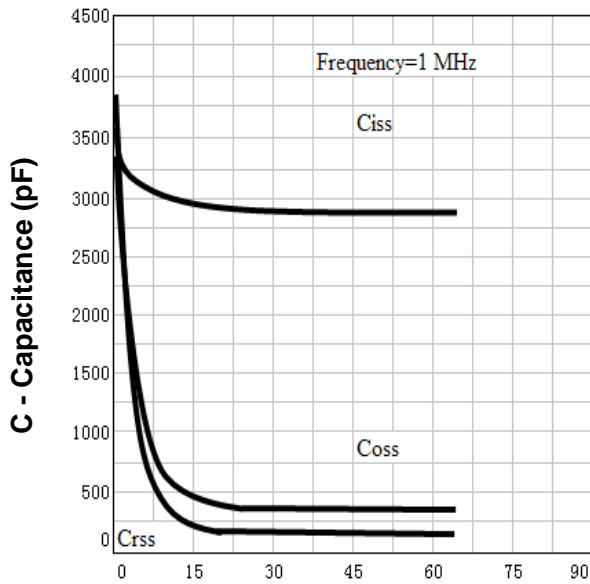
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



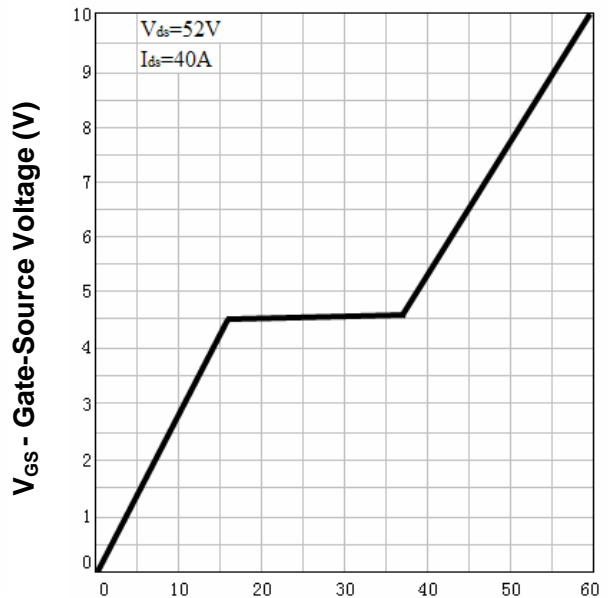
V_{SD} - Source-Drain Voltage (V)

Capacitance



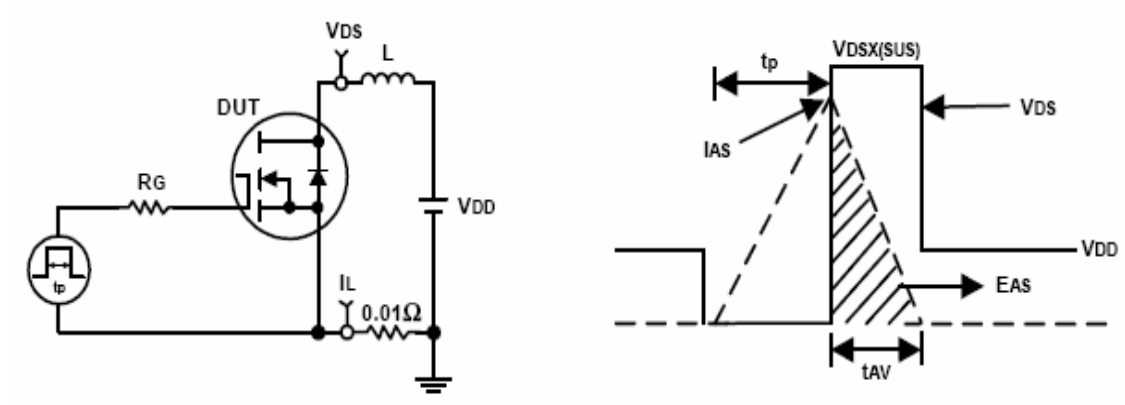
V_{DS} - Drain-Source Voltage (V)

Gate Charge

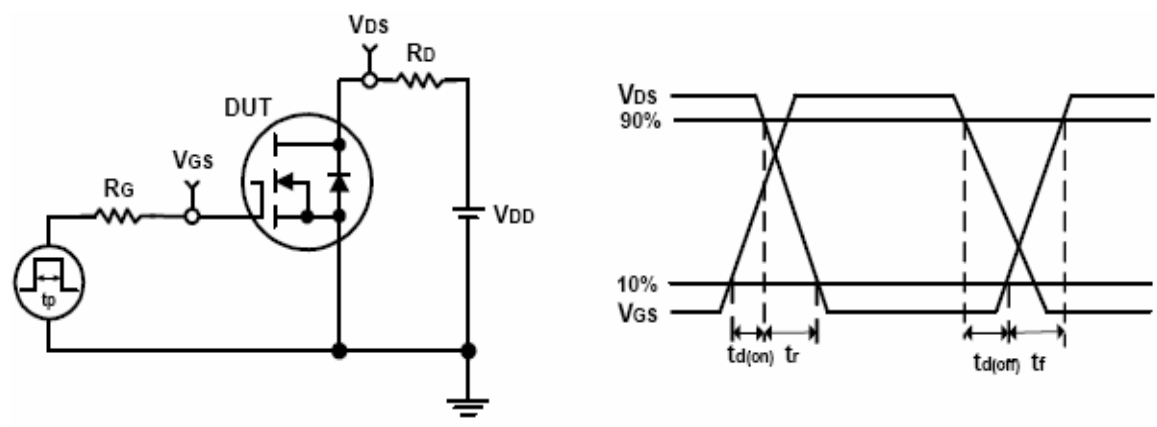


Q_G - Gate Charge (nC)

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information**RU6588****Package (Available)**

R : TO220

Operating Temperature Range

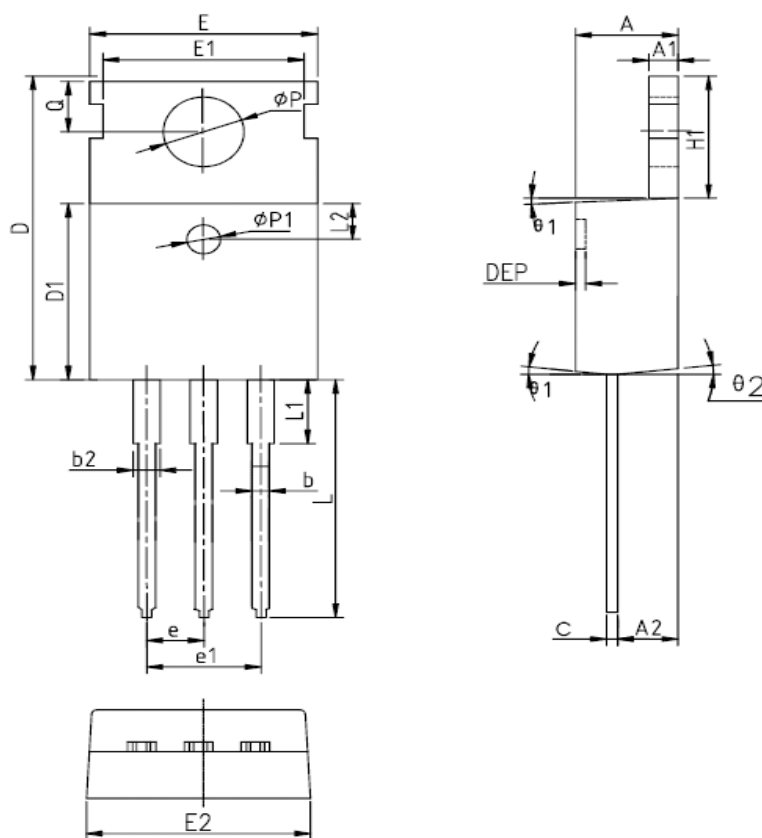
C : -55 to 175 °C

Assembly Material

G : Green & Lead Free

Packaging

T : TUBE

Package Information
TO-220FB-3L


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	ϕ_{p1}	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	ϕ_p	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	θ_1	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	θ_2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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